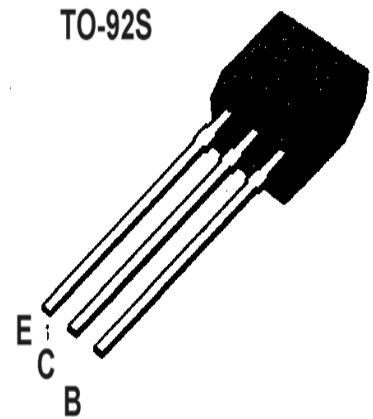


■ ■ APPLICATION: High Frequency Low Noise Amplifier Applications.

■ ■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EB0}	4	V
Collector current	I _c	0.02	A
Emitter current	I _e	-0.02	A
Collector Power Dissipation	P _c	0.4	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■ ■ ELECTRICAL CHARACTERISTICS (Ta=25°C, R_G=10KΩ)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV _{cbo}	40			V	I _c =50uA	I _e =0	
Collector-Emitter Breakdown Voltage	BV _{ceo}	30			V	I _c =1mA	I _b =0	
Emitter-Base Breakdown Voltage	BV _{ebo}	4			V	I _e =50uA	I _c =0	
Collector Cut-off Current	I _{cbo}			0.5	uA	V _{cb} =40V	I _e =0	
Emitter Cut-off Current	I _{ebo}			0.5	uA	V _{eb} =4V	I _c =0	
DC Current Gain	h _{FE}	40		200	β	V _{ce} =6V	I _c =1mA	
Gain bandwidth product	f _T	300	550		MHz	V _{ce} =6V	I _c =1mA	
Reverse Transfer Capacitance	C _{re}		0.70		pF	V _{cb} =6V	I _e =0	f=1MHz
Noise Figure	NF		2.5	5	dB	V _{ce} =6V	I _e =-1mA	f=100MHz
Power Gain	G _{pe}		18					

■ ■ h_{FE} Classification And Marking

Print Mark	C3195S		
Classification	R	O	Y
h _{FE}	40~80	70~140	100~200